



MC-01-1488

December 15, 2003

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/666,359 09/19/03 |

Chi-Chun Chen et al.

METHOD OF FORMING AN ULTRATHIN
NITRIDE/OXIDE STACK AS A GATE
DIELECTRIC

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on December 19, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

SB Ackerman 12/19/03

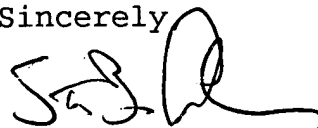
U.S. Patent 6,228,779 to Bloom et al., "Ultra Thin Oxynitride and Nitride/Oxide Stacked Gate Dielectrics Fabricated by High Pressure Technology," describes an SiON and ON stack gate dielectric high pressure process.

U.S. Patent 6,017,791 to Wang et al., "Multi-Layer Silicon Nitride Deposition Method for Forming Low Oxidation Temperature Thermally Oxidized Silicon Nitride/Silicon Oxide (NO) Layer," describes an ON process for a gate dielectric.

U.S. Patent 6,020,238 to He et al., "Method of Fabricating a High Dielectric Constant Interpolysilicon Dielectric Structure for a Low Voltage Non-Volatile Memory", describes a high-k (high dielectric constant) gate dielectric process for a low voltage non-volatile memory.

U.S. Patent 5,464,792 to Tseng et al., "Process to Incorporate Nitrogen at an Interface of a Dielectric Layer in a Semiconductor Device," describes a process to incorporate nitrogen at an interface of a dielectric layer in a semiconductor device.

Sincerely

A handwritten signature in black ink, appearing to read 'S. B. Ackerman', with a stylized flourish at the end.

Stephen B. Ackerman,
Reg. No. 37761

Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)	Dossier Number (Optional) TSMC-01-1488	Application Number 10/666,359
	Applicant Chi-Chun Chen et al.	
	Filing Date 09/19/03	Group Art Unit

U. S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

[illegible]

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.